

General Description

The TF050P03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

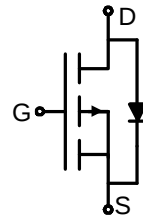
Features

Advance high cell density Trench technology
Low $R_{DS(ON)}$ to minimize conductive loss
Low Gate Charge for fast switching
Low Thermal resistance

Application

MB/VGA Vcore
SMPS 2nd Synchronous Rectifier
POL application
BLDC Motor driver

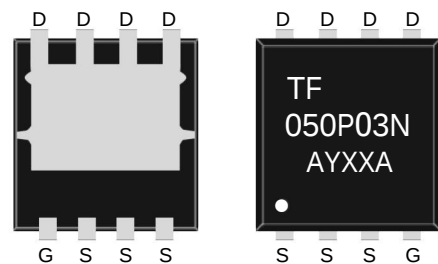
Product Summary



$$V_{DS} = -30V \quad I_D = -80A$$

$$R_{DS(ON)}(-10V \text{ typ}) = 4.3m\Omega$$

$$R_{DS(ON)}(-4.5V \text{ typ}) = 5.7m\Omega$$



PDFNWB5x6-8L

Ordering Information:

Part NO.	TF050P03N
Marking1	050P03N
Marking2	TF:tuofeng; Y:year code; XX:Week; AA:device code;
Basic ordering unit (pcs)	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@T_C=25^\circ C}$	-80	A
	$I_{D@T_C=75^\circ C}$	-56	A
	$I_{D@T_C=100^\circ C}$	-48	A
Pulsed Drain Current ^①	I_{DM}	-210	A
Total Power Dissipation ^②	$P_D@T_C=25^\circ C$	70	W
Total Power Dissipation	$P_D@T_A=25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

● Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	4.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	45	° C/W
Soldering temperature, wavesoldering for 8s	T _{sold}	-	-	265	° C

● Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-1.00	-1.50	-2.00	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -20A		4.3	5.5	mΩ
		V _{GS} = -4.5V, I _D = -15A		5.7	7.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -20V, I _D = -20A		12		S
Source-drain voltage	V _{SD}	I _S = -20A		0.85	1.00	V

● Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DD} = -15V V _{GS} = 0V	-	4646	-	pF
Output capacitance	C _{oss}		-	617.8	-	
Reverse transfer capacitance	C _{rss}		-	601.2	-	

● Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = -20V I _D = -20A V _{GS} = -10V	-	83.6	-	nC
Gate - Source charge	Q _{gs}		-	18.7	-	
Gate - Drain charge	Q _{gd}		-	9.50	-	
Body Diode Reverse Recovery Time	T _{rr}	I _F = 10A, di/dt = 100A/μs		25		nS
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 10A, di/dt = 100A/μs		78		nC

Note:

① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

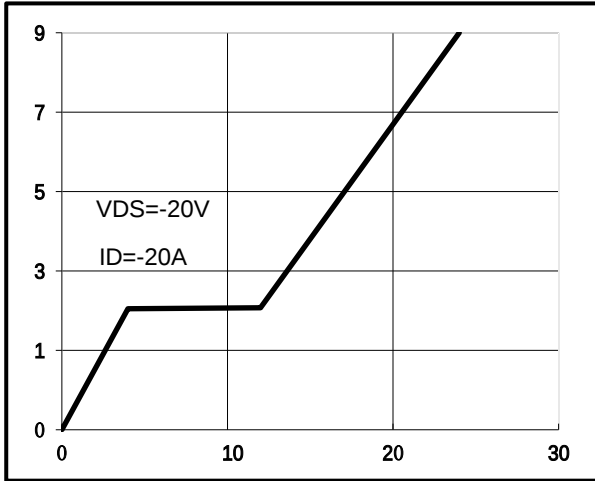


Fig.2 Capacitance Characteristics

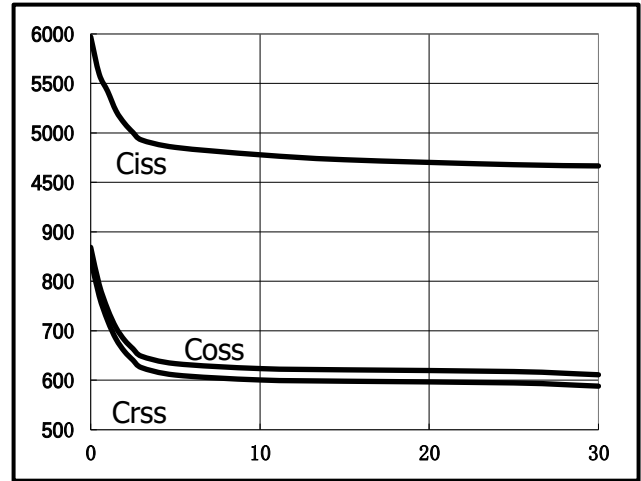


Fig.3 Power Dissipation Derating Curve

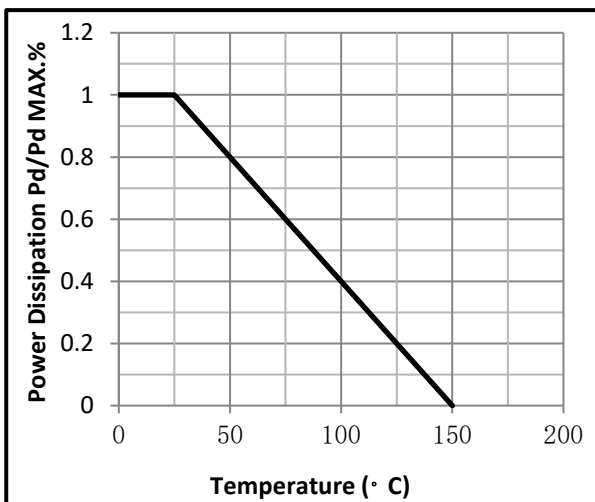


Fig.4 Typical output Characteristics

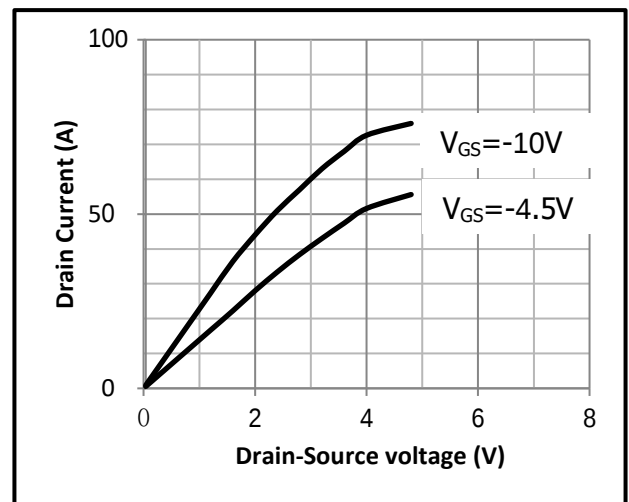


Fig.5 Threshold Voltage V.S Junction Temperature

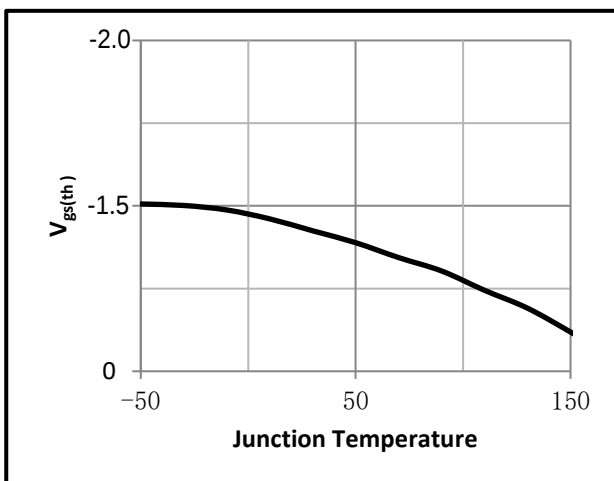


Fig.6 Resistance V.S Drain Current

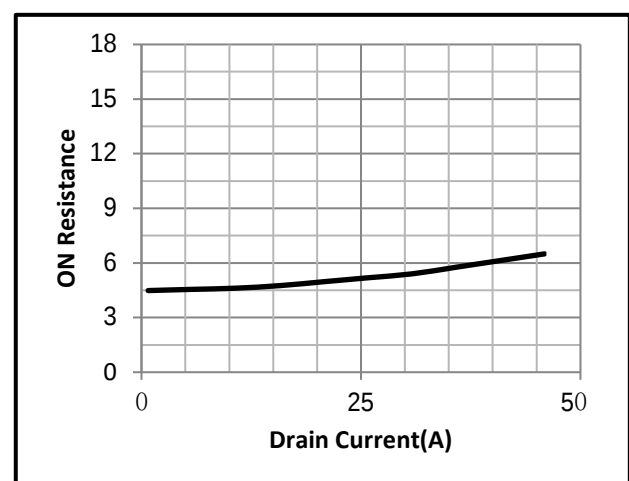


Fig.7 On-Resistance VS Gate Source Voltage

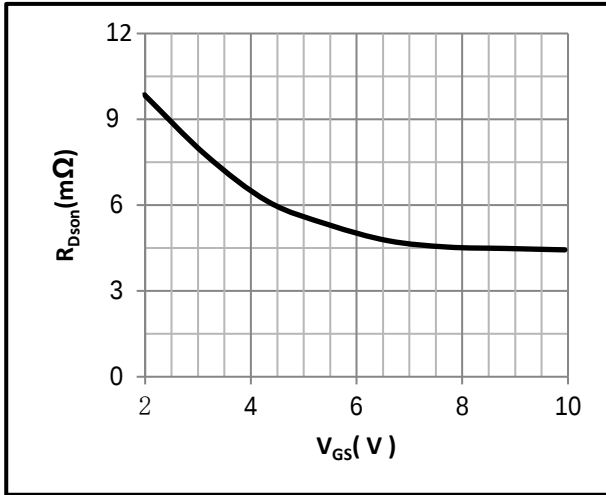


Fig.8 On-Resistance V.S Junction Temperature

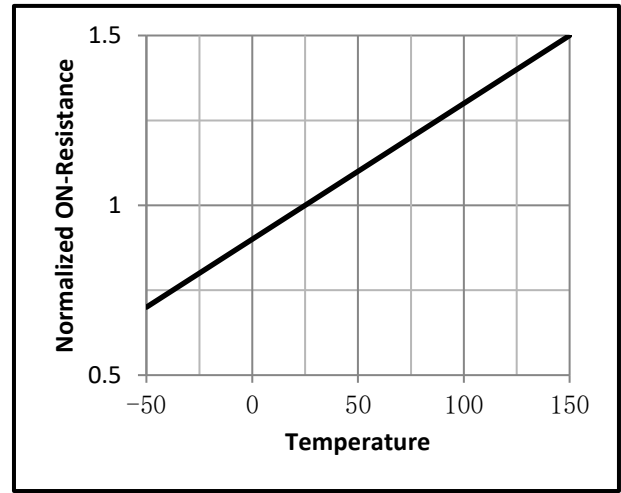


Fig.9 Switching Time Measurement Circuit

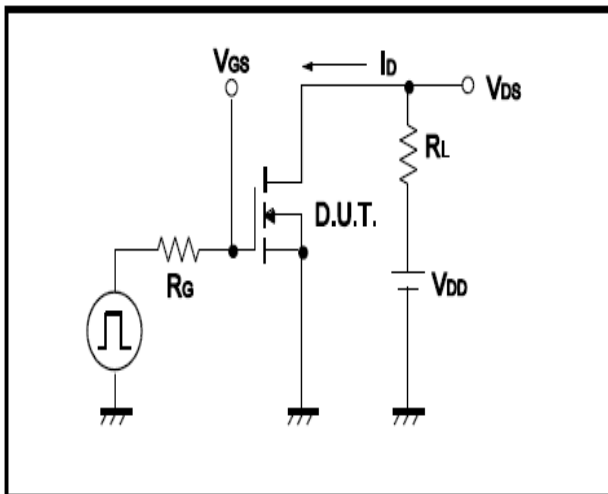


Fig.10 Gate Charge Waveform

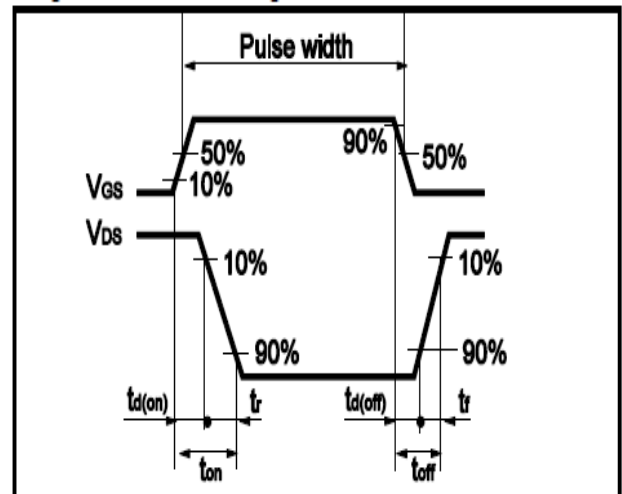


Fig.11 Avalanche Measurement Circuit

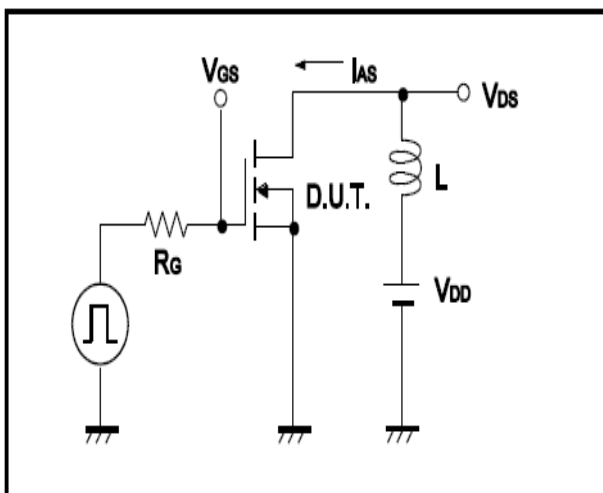
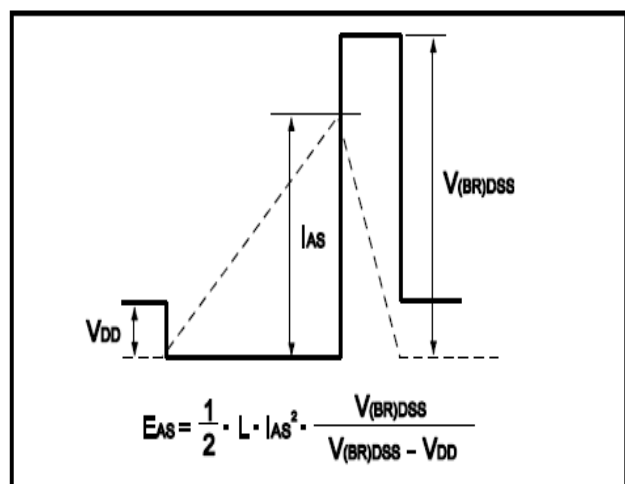
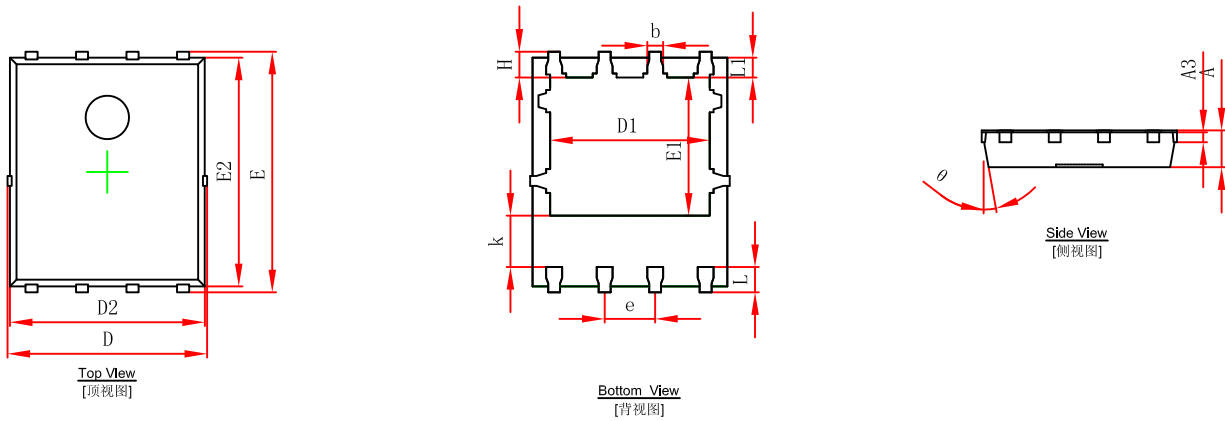


Fig.12 Avalanche Waveform

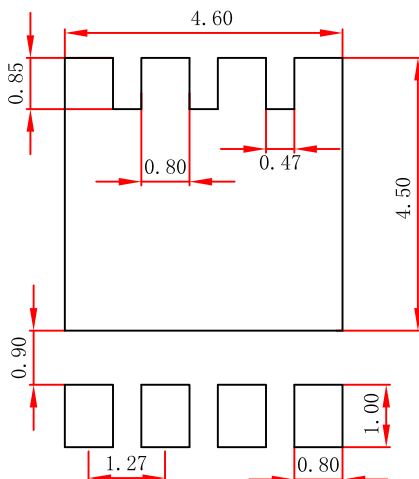


PDFNWB5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.